## Summary

This is a Preliminary Amendment for the above-cited application. Should the Examiner have any questions or suggestions regarding the prosecution of this application, he is asked to contact applicants' representative at the telephone number listed below.

Respectfully submitted,

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Reg. No. 42,127

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Marked up copy of the amendment

- 3. (Amended) The memory element of claim [2]  $\underline{1}$ , wherein said second region is [adjacent to said edge portion, said first region is remote to said edge portion] doped differently from said first region.
- 6. (Amended) The memory element of claim 1, wherein said [second region is adjacent to said edge portion, said first region is remote to said edge portion] conductive sidewall spacer comprises polysilicon.
- 12. (Amended) The memory element of claim 1, wherein said conductive sidewall spacer includes at least one [columnar portion protruding toward said memory material] raised portion extending to an end adjacent to said memory material.
- 16. (Amended) The memory element of claim [15]  $\underline{14}$ , wherein said second region is [adjacent to said edge portion, said first region is remote to said edge portion]  $\underline{doped}$  differently from said first region.

- 19. (Amended) The memory element of claim [18]  $\underline{14}$ , wherein said [memory material is adjacent to at least a portion of an edge of said conductive liner] conductive liner comprises polysilicon.
- 25. (Amended) The memory element of claim 14, wherein said conductive liner includes at least one [columnar portion protruding toward said memory material] raised portion extending to an end adjacent said memory material.